16Mb (512K x 2Banks×16) Synchronous SDRAM

Descriptions

The H2A116M1633B is Synchronous Dynamic Random Access Memory (SDRAM) organized as 512K words x 2 banks by 16 bits. All inputs and outputs are synchronized with the positive edge of the clock.

The 16Mb SDRAM uses synchronized pipelined architecture to achieve high speed data transfer rates and is designed to operate at 3.3V low power memory system. It also provides auto refresh with power saving / down mode. All inputs and outputs voltage levels are compatible with LVTTL.

Available packages:TSOPII 50P 400mil.

Features

• Fully Synchronous to Positive Clock Edge

• Single 3.3V ±0.3V Power Supply

• LVTTL Compatible with Multiplexed Address

• Programmable Burst Length (B/L) - 1, 2, 4, 8 or Full Page

• Programmable CAS Latency (C/L) - 3

• Data Mask (DQM) for Read / Write Masking

• Programmable Wrap Sequence

– Sequential (B/L = 1/2/4/8/full Page)

– Interleave (B/L = 1/2/4/8)

• Burst Read with Single-bit Write Operation

• All Inputs are Sampled at the Rising Edge of the System Clock

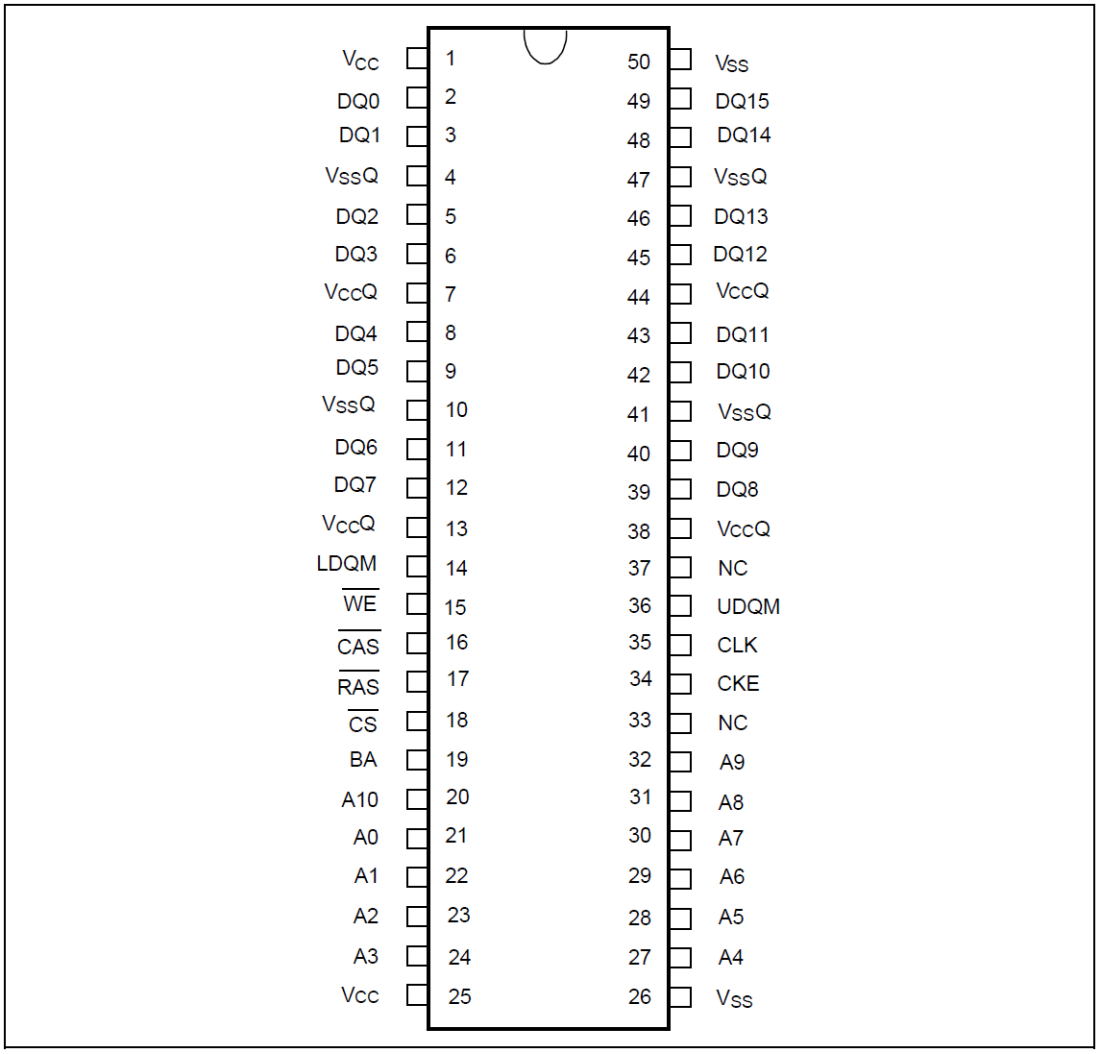
• Auto Refresh and Self Refresh

• 2,048 Refresh Cycles / 32ms (15.625us)

Ordering Information

Part No	Organization	Max. Freq	Package	Grade
H2A116M1633BL1C	1M X 16	SDR-143MHz (3-3-3)	50pin TSOP(II)	Commercial
H2A116M1633BM1C	1M X 16	SDR-166MHz (3-3-3)	50pin TSOP(II)	Commercial

Pin Assignment



50pin TSOP-II / (400mil × 825mil) / (0.8mm Pin pitch)

Pin Description (Simplified)

Pin	Name	Function
20−24, 27−32	A0−A10	**(Address)** Multiplexed pins for row and column address. Row address: A0−A10. Column address: A0−A7.
19	BA	**(Bank Select)** Selects chip when active
2, 3, 5, 6, 8, 9, 11, 12, 39, 40, 42, 43, 45, 46, 48, 49	DQ0−DQ15	**(Data Input/ Output)** Multiplexed pins for data input and output.
18	/CS	**(Chip Select)** Disable or enable the command decoder. When command decoder is disabled, new command is ignored and previous operation continues.
17	/RAS	**(Row Address Strobe)** Command input. When sampled at the rising edge of the clock, /RAS, /CAS and /WE define the operation to be executed.
16	/CAS	**(Column Address Strobe)** Referred to /RAS
15	/WE	**(Write Enable)** Referred to /RAS
36, 14	UDQM/ LDQM	**(Input/Output Mask)** The output buffer is placed at Hi-Z (with latency of 2) when DQM is sampled high in read cycle. In write cycle, sampling DQM high will block the write operation with zero latency.
35	CLK	**(Clock Inputs)** System clock used to sample inputs on the rising edge of clock.
34	CKE	**(Clock Enable)** CKE controls the clock activation and deactivation. When CKE is low, Power Down mode, Suspend mode, or Self Refresh mode is entered.
1, 25	V_{CC}	**(Power)** Power for input buffers and logic circuit inside DRAM.
26, 50	V_{SS}	**(Ground)** Ground for input buffers and logic circuit inside DRAM.
7, 13, 38, 44	V_{CCQ}	**(Power for I/O buffer)** Separated power from VCC, used for output buffers to improve noise immunity.
4, 10, 41, 47	V_{SSQ}	**(Ground for I/O Buffer)** Separated ground from VSS, used for output buffers to improve noise immunity.
33, 37	NC	**(No Connection)** No connection.

Absolute Maximum Rating

Symbol	Item	Rating		Units
V_{IN}, V_{OUT}	Input, Output Voltage	-1 ~ V_{DD}+0.3		V
V_{CC}, V_{CCQ}	Power Supply Voltage	-1 ~ +4.6		V
T_{OPR}	Operating Temperature Range	Commercial	0 ~ +70	°C
T_{STG}	Storage Temperature Range	-55 ~ +150		°C
T_{SOLDER}	Soldering Temperature (10s)	260		˚C
P_D	Power Dissipation	1		W
I_{OUT}	Short Circuit Current	50		mA

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

Capacitance (V_{CC}=3.3V, f=1MHz, T_A=25°C)

Symbol	Parameter	Min.	Max.	Units
C_{CLK}	Input Capacitance (CLK)	-	4	pF
C_I	Input Capacitance (A0 to A10, BA, /CS, /RAS, /CAS , /WE, UDQM, LDQM, CKE)	-	4	pF
C_{IO}	Input/Output Capacitance (DQ0 to DQ15)	-	5.5	pF

Note: These parameters are periodically sampled and not 100% tested

Recommended DC Operating Conditions (T_A=-0°C ~+70°C)

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{CC}	Power Supply Voltage	3.0	3.3	3.6	V
V_{CCQ}	Power Supply Voltage (for I/O Buffer)	3.0	3.3	3.6	V
V_{IH}	Input Logic High Voltage	2.0		V_{DD}+0.3	V
V_{IL}	Input Logic Low Voltage	-0.3		0.8	V

Note: * All voltages referred to V_{SS}.

* V_{IH} (max.) = V_{CC} / V_{CCQ} +1.5V for pulse width ≦ 5ns

* V_{IL} (min.) = V_{CC} / V_{SSQ} -1.5V for pulse width ≦ 5ns

DC Characteristics

(V_{DD}=3.3V±0.3V, T_A=0°C ~ 70°C)

Symbol	Parameter	Test Conditions	Max.		Units
			143	166	
I_{CC1}	Operating Current tCK = min., tRC = min. Active precharge command cycling without burst operation ***(Note 3)***	1 Bank Operation	50	60	mA
I_{CC2}	Standby Current tCK = min., /CS = VIH VIH /L = VIH (min.) / VIL (max.) Bank: inactive state ***(Note 3)***	CKE = VIH	25	30	mA
I_{CC2P}		CKE = VIL (Power Down mod	2	2	mA
I_{CC2S}	Standby Current CLK = VIL, CS = VIH VIH/L = VIH (min.) / VIL (max.) Bank: inactive state ***(Note 3)***	CKE = VIH	10	10	mA
I_{CC2PS}		CKE = VIL (Power Down mode)	2	2	mA
I_{CC3}	No Operating Current tCK = min., /CS = VIH (min.) Bank: active state (2 Banks)	CKE = VIH	35	40	mA
I_{CC3P}		CKE = VIL (Power Down mode)	10	10	mA
I_{CC4}	Burst Operating Current (tCK = min.) Read/ Write command cycling ***(Note 3,4)***		100	110	mA
I_{CC5}	Auto Refresh Current (tCK = min.) Auto refresh command cycling ***(Note 3)***		50	55	mA
I_{CC6}	Self Refresh Current (CKE = 0.2V) Self refresh mode		2	2	mA

Note 1: Operation exceeds " Absolute Maximum Ratings " may cause permanent damage to the devices.

Note 2: All voltages are referenced to VSS

- 2.7V~3.6V power supply for -7/-7I speed grade.
- 3.3V ± 0.3V power supply for -5/-6/-6I/-6A speed grades.

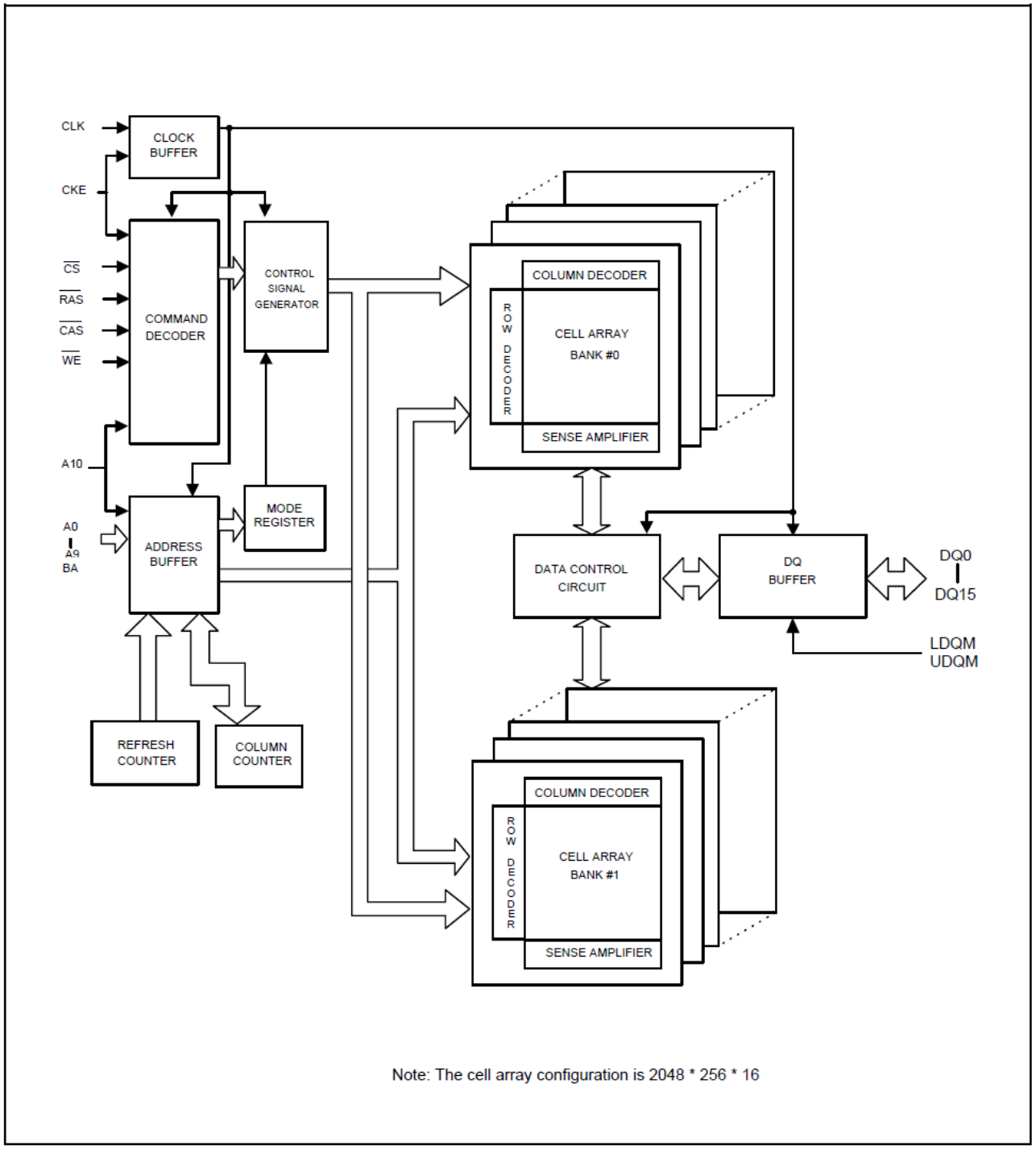
Note 3: These parameters depend on the cycle rate and listed values are measured at a cycle rate with the minimum values of tCK and tRC.

Note 4: These parameters depend on the output loading conditions. Specified values are obtained with output open.

DC Characteristics (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{IL}	Input Leakage Current	$0 \le V_I \le V_{DDQ}$, $V_{DDQ}=V_{DD}$ All other pins not under test=0V	-5	-	5	uA
I_{OL}	Output Leakage Current	$0 \le V_O \le V_{DDQ}$, D_{OUT} is disabled	-5	-	5	uA
V_{OH}	High Level Output Voltage	I_O=-4mA	2.4	-	-	V
V_{OL}	Low Level Output Voltage	I_O=+4mA	-	-	0.4	V

Block Diagram

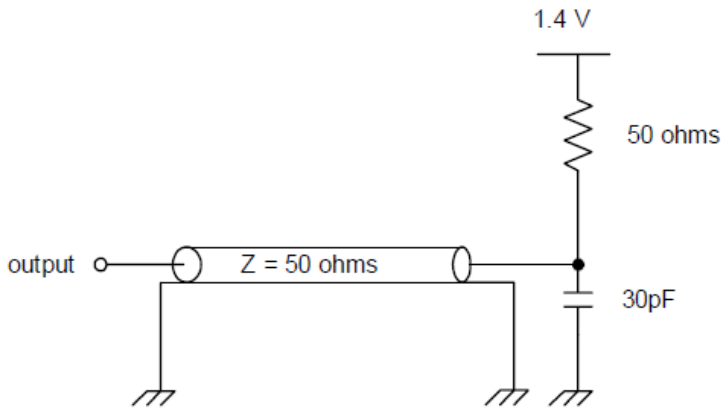


Note: The cell array configuration is 2048 * 256 * 16

AC Operating Test Conditions

(V_{DD}=3.3V±0.3V, T_A=0°C ~70°C)

Item	Conditions
Output Reference Level	1.4V/1.4V
Output Load	See diagram as below
Input Signal Level	2.4V/0.4V
Transition Time of Input Signals	2ns
Input Reference Level	1.4V



AC TEST LOAD

AC Characteristics

(V_{DD}=3.3V±0.3V, T_A=0°C ~70°C)

Symbol	Parameter	166 MHz		143 MHz		Units
		Min.	Max.	Min.	Max.	
t_{OH}	Output Data Hold Time ***(Note 7)***	2		2		ns
t_{HZ}	Output Data High Impedance Time ***(Note 5)***	2	6	2.5	7	ns
t_{LZ}	Output Data Low Impedance Time ***(Note 7)***	0		0		ns
t_{SB}	Power Down Mode Entry Time	0	6	0	7	ns
t_{DS}	Data-in-Set-up Time ***(Note 6)***	1.5		1.5		ns
t_{DH}	Data-in Hold Time ***(Note 6)***	0.7		1		ns
t_{AS}	Address Set-up Time ***(Note 6)***	1.5		1.5		ns
t_{AH}	Address Hold Time ***(Note 6)***	0.7		1		ns
t_{CKS}	CKE Set-up Time ***(Note 6)***	1.5		1.5		ns
t_{CKH}	CKE Hold Time ***(Note 6)***	0.7		1		ns
t_{CMS}	Command Set-up Time ***(Note 6)***	1.5		1.5		ns
t_{CMH}	Command Hold Time ***(Note 6)***	0.7		1		ns
t_{REF}	Refresh Time		64		64	Ms
t_{RSC}	Mode Register Set Cycle Time	2		2		t_{CK}
t_{XSR}	Exit self refresh to ACTIVE command	72		75		ns

* All voltages referenced to V_{SS}.

AC Characteristics (Continued)

(V_{DD}=3.3V±0.3V, T_A=0°C ~70°C)

Symbol	Parameter		166 MHz		143 MHz		Units
			Min.	Max.	Min.	Max.	
t_{RC}	Ref/Active to Ref/Active Command Period		60		65		ns
t_{RAS}	Active to Precharge Command Period		42	100k	45	100k	ns
t_{RCD}	Active to Read/Write Command Delay Time		18		20		ns
t_{CCD}	Read/Write(a) to Read/Write(b) Command Period		1		1		t_{CK}
t_{RP}	Precharge to Active(b) Command Period		18		18		ns
t_{RRD}	Active(a) to Active(b) Command Period		12		14		ns
t_{WR}	Write Recovery Time	CL=3	2		2		t_{CK}
t_{CK}	CLK Cycle Time	CL=3	6	1K	7	1K	ns
t_{CH}	CLK High Level Width ***(Note 6)***		2		2		ns
t_{CL}	CLK Low Level Width ***(Note 6)***		2		2		ns
t_{AC}	Access Time from CLK ***(Note 7)***	CL=3		5		5	ns

* All voltages referenced to V_{SS}.

Note 5: t_{HZ} defines the time at which the outputs achieve the open circuit condition and is not referenced to output level.

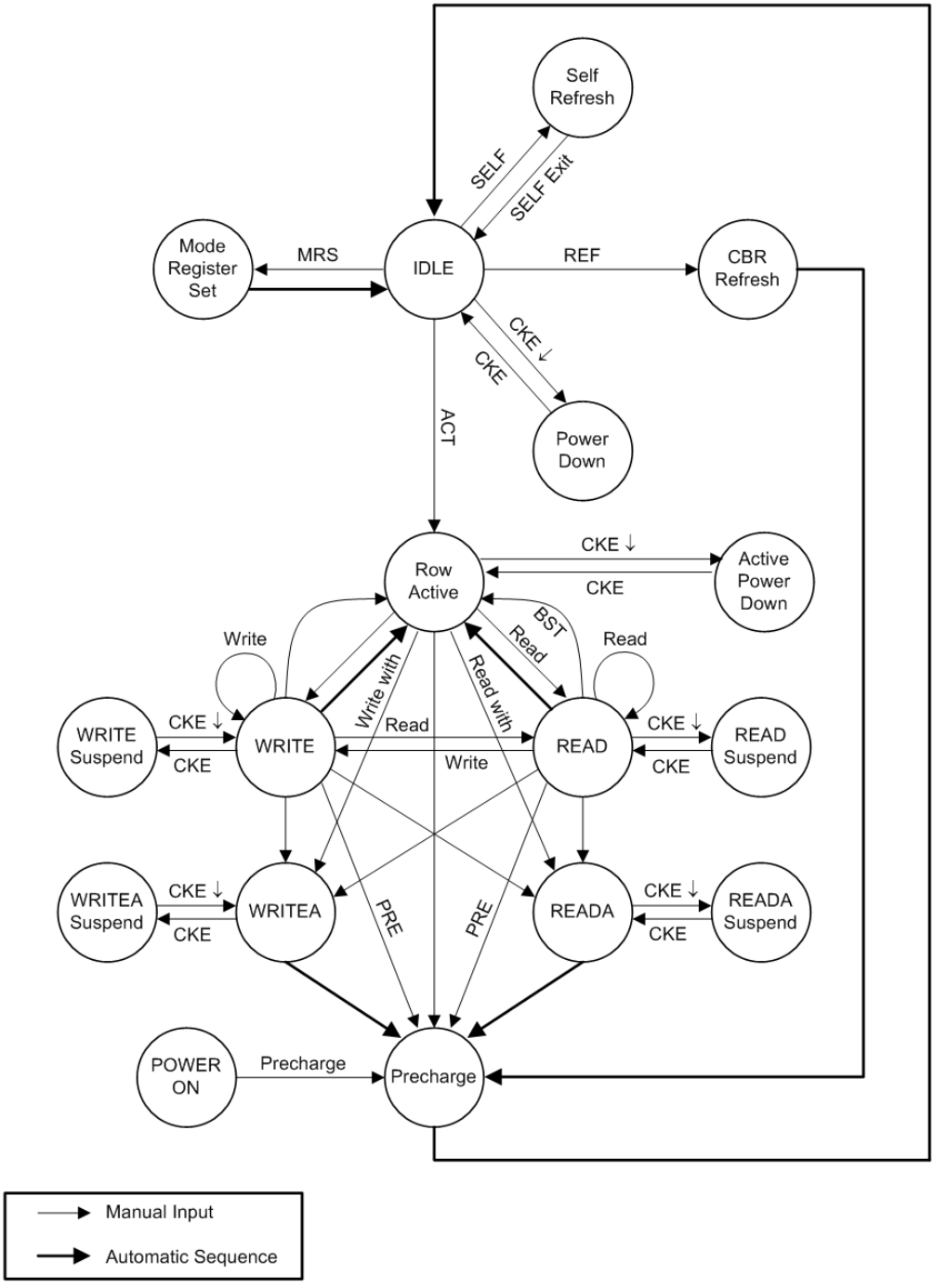
Note 6: Assumed input rise and fall time (t_T) = 1nS.
If tr & tf is longer than 1nS, transient time compensation should be considered,
i.e., [(tr + tf)/2-1]nS should be added to the parameter
(The t_T maximum can't be more than 10nS for low frequency application.)

Note 7: If clock rising time (t_T) is longer than 1nS, (t_T/2-0.5)nS should be added to the parameter.

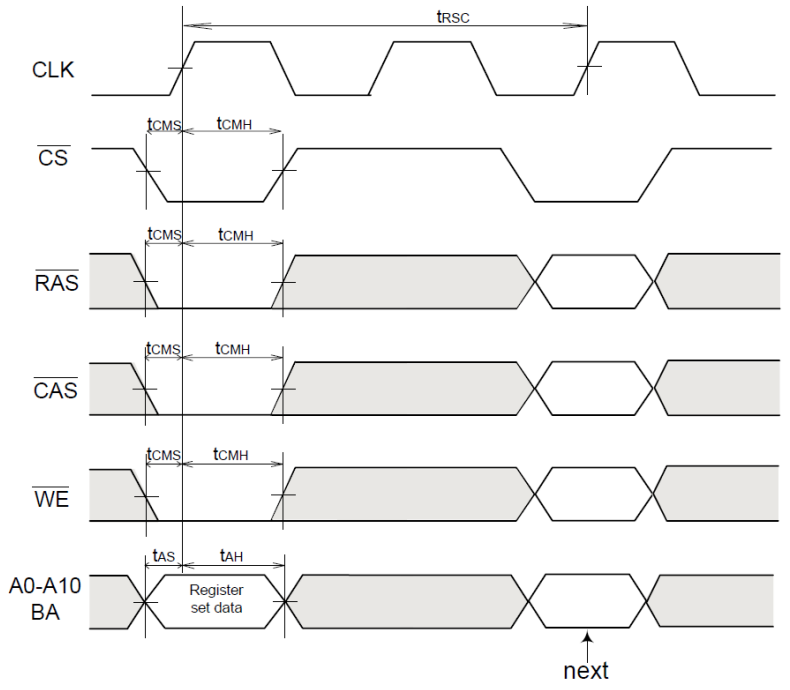
Recommended Power On and Initialization

The following power on and initialization sequence guarantees the device is preconditioned to each user's specific needs. (Like a conventional DRAM) During power on, all V_{DD} and V_{DDQ} pins must be built up simultaneously to the specified voltage when the input signals are held in the "NOP" state. The power on voltage must not exceed V_{DD}+0.3V on any of the input pins or V_{DD} supplies. (CLK signal started at same time) After power on, an initial pause of 200 µs is required followed by a precharge of all banks using the precharge command.
To prevent data contention on the DQ bus during power on, it is required that the DQM and CKE pins be held high during the initial pause period. Once all banks have been precharged, the Mode Register Set Command must be issued to initialize the Mode Register. A minimum of eight Auto Refresh cycles (CBR) are also required, and these may be done before or after programming the Mode Register.

Simplified State Diagram



Address Input for Mode Register Set



A0	Burst Length	
A1		
A2		
A3	Addressing Mode	
A4	CAS Latency	
A5		
A6		
A7	"0"	(Test Mode)
A8	"0"	Reserved
A9	Write Mode	
A10	"0"	Reserved
BA	"0"	

			Burst Length	
A2	A1	A0	Sequential	Interleave
0	0	0	1	1
0	0	1	2	2
0	1	0	4	4
0	1	1	8	8
1	0	0	Reserved	Reserved
1	0	1		
1	1	0		
1	1	1	Full Page	

A3	Addressing Mode
0	Sequential
1	Interleave

A6	A5	A4	CAS Latency
0	0	0	Reserved
0	0	1	Reserved
0	1	0	2
0	1	1	3
1	0	0	Reserved

A9	Single Write Mode
0	Burst read and Burst write
1	Burst read and single write

Burst Type (A3)

Burst Length	A2	A1	A0	Sequential Addressing	Interleave Addressing
2	X	X	0	0 1	0 1
	X	X	0	1 0	1 0
4	X	0	0	0 1 2 3	0 1 2 3
	X	0	1	1 2 3 0	1 0 3 2
	X	1	0	2 3 0 1	2 3 0 1
	X	1	1	3 0 1 2	3 2 1 0
8	0	0	0	0 1 2 3 4 5 6 7	0 1 2 3 4 5 6 7
	0	0	1	1 2 3 4 5 6 7 0	1 0 3 2 5 4 7 6
	0	1	0	2 3 4 5 6 7 0 1	2 3 0 1 6 7 4 5
	0	1	1	3 4 5 6 7 0 1 2	3 2 1 0 7 6 5 4
	1	0	0	4 5 6 7 0 1 2 3	4 5 6 7 0 1 2 3
	1	0	1	5 6 7 0 1 2 3 4	5 4 7 6 1 0 3 2
	1	1	0	6 7 0 1 2 3 4 5	6 7 4 5 2 3 0 1
	1	1	1	7 0 1 2 3 4 5 6	7 6 5 4 3 2 1 0
Full Page*	n	n	n	Cn Cn+1 Cn+2……	-

* Page length is a function of I/O organization and column addressing ×16 (CA0 ~ CA7): Full page = 256bits

1. Command Truth Table

Command	Symbol	CKE		/CS	/RAS	/CAS	/WE	BA0, BA1	A10	A11, A9~A10
		n-1	n							
Ignore Command	DESL	H	X	H	X	X	X	X	X	X
No Operation	NOP	H	X	L	H	H	H	X	X	X
Burst Stop	BSTH	H	X	L	H	H	L	X	X	X
Read	READ	H	X	L	H	L	H	V	L	V
Read with Auto Pre-charge	READA	H	X	L	H	L	H	V	H	V
Write	WRIT	H	X	L	H	L	L	V	L	V
Write with Auto Pre-charge	WRITA	H	X	L	L	H	H	V	H	V
Bank Activate	ACT	H	X	L	L	H	H	V	V	V
Pre-charge Select Bank	PRE	H	X	L	L	H	L	V	L	X
Pre-charge All Banks	PALL	H	X	L	L	H	L	X	H	X
Mode Register Set	MRS	H	X	L	L	L	L	L	L	V

H = High level, L = Low level, X = High or Low level (Don't care), V = Valid data input

2. DQM Truth Table

Command	Symbol	CKE		/CS
		n-1	n	
Upper Byte Write Enable/Output Enable	BSTH	H	X	L
Read	READ	H	X	L
Read with Auto Pre-charge	READA	H	X	L
Write	WRIT	H	X	L
Write with Auto Pre-charge	WRITA	H	X	L
Bank Activate	ACT	H	X	L
Pre-charge Select Bank	PRE	H	X	L
Pre-charge All Banks	PALL	H	X	L
Mode Register Set	MRS	H	X	L
Data Write/Output Enable	ENB	H	X	H
Data Mask/Output Disable	MASK	H	X	L

H = High level, L = Low level, X = High or Low level (Don't care), V = Valid data input

3. CKE Truth Table

Item	Command	Symbol	CKE		/CS	/RAS	/CAS	/WE	Addr.
			n-1	n					
Activating	Clock Suspend Mode Entry		H	L	X	X	X	X	X
Any	Clock Suspend Mode		L	L	X	X	X	X	X
Clock Suspend	Clock Suspend Mode Exit		L	H	X	X	X	X	X
Idle	CBR Refresh Command	REF	H	H	L	L	L	H	X
Idle	Self Refresh Entry	SELF	H	L	L	L	L	H	X
Self Refresh	Self Refresh Exit		L	H	L	H	H	H	X
			L	H	H	X	X	X	X
Idle	Power Down Entry		H	L	X	X	X	X	X
Power Down	Power Down Exit		L	H	X	X	X	X	X

H = High level, L = Low level, X = High or Low level (Don't care)

4. Operative Command Table

Current State	/CS	/R	/C	/W	Addr.	Command	Action
Idle	H	X	X	X	X	DESL	Nop or power down ***(Note 8)***
	L	H	H	X	X	NOP or BST	Nop or power down ***(Note 8)***
	L	H	L	H	BA/CA/A10	READ/READA	ILLEGAL ***(Note 9)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	ILLEGAL ***(Note 9)***
	L	L	H	H	BA/RA	ACT	Row activating
	L	L	H	L	BA, A10	PRE/PALL	Nop
	L	L	L	H	X	REF/SELF	Refresh or self refresh ***(Note 10)***
	L	L	L	L	Op-Code	MRS	Mode register accessing
Row Active	H	X	X	X	X	DESL	Nop
	L	H	H	X	X	NOP or BST	Nop
	L	H	L	H	BA/CA/A10	READ/READA	Begin read: Determine AP ***(Note 11)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	Begin write: Determine AP ***(Note 11)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	Pre-charge ***(Note 12)***
	L	L	L	H	X	REF/SELF	ILLEGAL ***(Note 10)***
	L	L	L	L	Op-Code	MRS	ILLEGAL
Read	H	X	X	X	X	DESL	Continue burst to end → Row active
	L	H	H	H	X	NOP	Continue burst to end → Row active
	L	H	H	L	X	BST	Burst stop → Row active
	L	H	L	H	BA/CA/A10	READ/READA	Terminate burst, new read: Determine AP ***(Note 13)***
	L	L	L	L	BA/CA/A10	WRIT/WRITA	Terminate burst, start write: Determine AP ***(Note 13,14)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	Terminate burst, pre-charging ***(Note 10)***
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL
Write	H	X	X	X	X	DESL	Continue burst to end → Write recovering
	L	H	H	H	X	NOP	Continue burst to end → Write recovering
	L	H	H	L	X	BST	Burst stop → Row active
	L	H	L	H	BA/CA/A10	READ/READA	Terminate burst, start read: Determine AP 7, 8 ***(Note 13,14)***
	L	L	L	L	BA/CA/A10	WRIT/WRITA	Terminate burst, new write: Determine AP 7 ***(Note 13)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	Terminate burst, pre-charging ***(Note 15)***
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL

H = High level, L = Low level, X = High or Low level (Don't care)

4. Operative Command Table (Continued)

Current State	/CS	/R	/C	/W	Addr.	Command	Action
Read with AP	H	X	X	X	X	DESL	Continue burst to end → Pre-charging
	L	H	H	H	X	NOP	Continue burst to end → Pre-charging
	L	H	H	L	X	BST	ILLEGAL
	L	H	L	H	BA/CA/A10	READ/READA	ILLEGAL ***(Note 9)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	ILLEGAL ***(Note 9)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	ILLEGAL ***(Note 9)***
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL
Write with AP	H	X	X	X	X	DESL	Burst to end → Write recovering with auto pre-charge
	L	H	H	H	X	NOP	Continue burst to end → Write recovering with auto pre-charge
	L	H	H	L	X	BST	ILLEGAL
	L	H	L	H	BA/CA/A10	READ/READA	ILLEGAL ***(Note 9)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	ILLEGAL ***(Note 9)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	ILLEGAL ***(Note 9)***
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL
Pre-charging	H	X	X	X	X	DESL	Nop → Enter idle after tRP
	L	H	H	H	X	NOP	Nop → Enter idle after tRP
	L	H	H	L	X	BST	ILLEGAL
	L	H	L	H	BA/CA/A10	READ/READA	ILLEGAL ***(Note 9)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	ILLEGAL ***(Note 9)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	Nop → Enter idle after tRP
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL
Row Activating	H	X	X	X	X	DESL	Nop → Enter idle after tRCD
	L	H	H	H	X	NOP	Nop → Enter idle after tRCD
	L	H	H	L	X	BST	ILLEGAL
	L	H	L	H	BA/CA/A10	READ/READA	ILLEGAL ***(Note 9)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	ILLEGAL ***(Note 9)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9,16)***
	L	L	H	L	BA, A10	PRE/PALL	ILLEGAL ***(Note 9)***
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL

H = High level, L = Low level, X = High or Low level (Don't care), AP = Auto Pre-charge

4. Operative Command Table (Continued)

Current State	/CS	/R	/C	/W	Addr.	Command	Action
Write Recovering	H	X	X	X	X	DESL	Nop → Enter row active after tDPL
	L	H	H	H	X	NOP	Nop → Enter row active after tDPL
	L	H	H	L	X	BST	Nop → Enter row active after tDPL
	L	H	L	H	BA/CA/A10	READ/READA	Start read, Determine AP
	L	H	L	L	BA/CA/A10	WRIT/WRITA	New write, Determine AP ***(Note 14)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	ILLEGAL ***(Note 9)***
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL
Write Recovering with AP	H	X	X	X	X	DESL	Nop → Enter pre-charge after tDPL
	L	H	H	H	X	NOP	Nop → Enter pre-charge after tDPL
	L	H	H	L	X	BST	Nop → Enter pre-charge after tDPL
	L	H	L	H	BA/CA/A10	READ/READA	ILLEGAL ***(Note 9,14)***
	L	H	L	L	BA/CA/A10	WRIT/WRITA	ILLEGAL ***(Note 9)***
	L	L	H	H	BA/RA	ACT	ILLEGAL ***(Note 9)***
	L	L	H	L	BA, A10	PRE/PALL	ILLEGAL
	L	L	L	H	X	REF/SELF	ILLEGAL
	L	L	L	L	Op-Code	MRS	ILLEGAL
Refreshing	H	X	X	X	X	DESL	Nop → Enter idle after tRC
	L	H	H	X	X	NOP/BST	Nop → Enter idle after tRC
	L	H	L	X	X	READ/WRIT	ILLEGAL
	L	L	H	X	X	ACT/PRE/PALL	ILLEGAL
	L	L	L	X	X	REF/SELF/MRS	ILLEGAL
Mode Register Accessing	H	X	X	X	X	DESL	Nop
	L	H	H	H	X	NOP	Nop
	L	H	H	L	X	BST	ILLEGAL
	L	H	L	X	X	READ/WRIT	ILLEGAL
	L	L	X	X	X	ACT/PRE/PALL/ REF/SELF/MRS	ILLEGAL

H = High level, L = Low level, X = High or Low level (Don't care), AP = Auto Pre-charge

Note 8: If all banks are idle, and CKE is inactive (Low level), SDRAM will enter Power down mode. All input buffers except CKE will be disabled.

Note 9: Illegal to bank in specified states;
Function may be legal in the bank indicated by Bank Address (BA), depending on the state of that bank.

Note 10: If all banks are idle, and CKE is inactive (Low level), SDRAM will enter Self refresh mode. All input buffers except CKE will be disabled.

Note 11: Illegal if t_{RCD} is not satisfied.

Note 12: Illegal if t_{RAS} is not satisfied.

Note 13: Must satisfy burst interrupt condition.

Note 14: Must satisfy bus contention, bus turn around, and/or write recovery requirements.

Note 15: Must mask preceding data which don't satisfy t_{DPL}.

Note 16: Illegal if t_{RRD} is not satisfied.

5. Command Truth Table for CKE

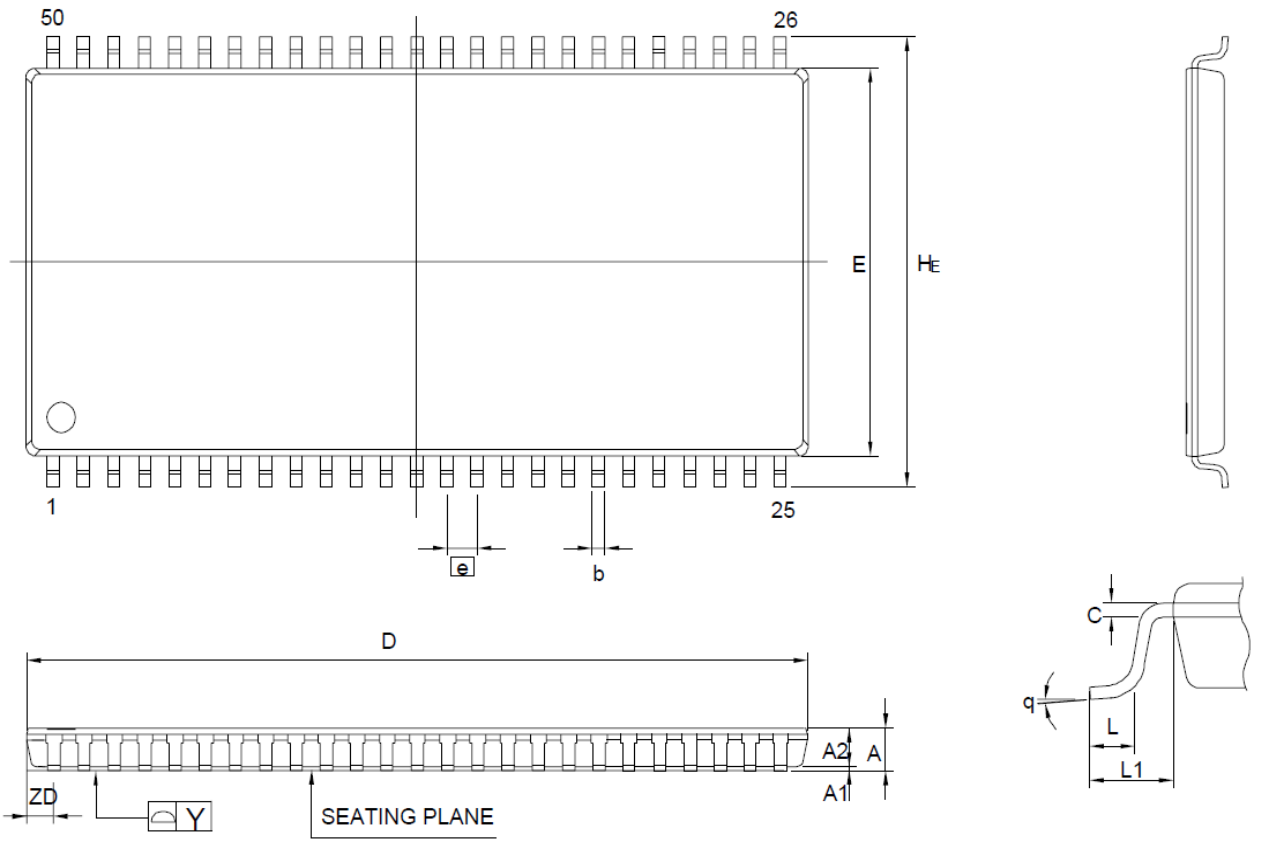
Current State	CKE		/CS	/R	/C	/W	Addr.	Action
	n-1	n						
Self Refresh	H	X	X	X	X	X	X	INVALID, CLK(n-1) would exit self refresh
	L	H	H	X	X	X	X	Self refresh recovery
	L	H	L	H	H	X	X	Self refresh recovery
	L	H	L	H	L	X	X	ILLEGAL
	L	H	L	L	X	X	X	ILLEGAL
	L	L	X	X	X	X	X	Maintain self refresh
Self Refresh Recovery	H	H	H	X	X	X	X	Idle after tRC
	H	H	L	H	H	X	X	Idle after tRC
	H	H	L	H	L	X	X	ILLEGAL
	H	H	L	L	X	X	X	ILLEGAL
	H	L	H	X	X	X	X	ILLEGAL
	H	L	L	H	H	X	X	ILLEGAL
	H	L	L	H	L	X	X	ILLEGAL
	H	L	L	L	X	X	X	ILLEGAL
Power Down	H	X	X	X	X	X	X	INVALID, CLK(n-1) would exit power down
	L	H	X	X	X	X	X	Exit power down → Idle
	L	L	X	X	X	X	X	Maintain power down mode
Both Banks Idle	H	H	H	X	X	X		Refer to operations in Operative Command Table
	H	H	L	H	X	X		
	H	H	L	L	H	X		
	H	H	L	L	L	H	X	Refresh
	H	H	L	L	L	L	Op-Code	Refer to operations in Operative Command Table
	H	L	H	X	X	X		
	H	L	L	H	X	X		
	H	L	L	L	H	X		
	H	L	L	L	L	H	X	Self refresh ***(Note 17)***
	H	L	L	L	L	L	Op-Code	Refer to operations in Operative Command Table
	L	X	X	X	X	X	X	Power down ***(Note 17)***
Row Active	H	X	X	X	X	X	X	Refer to operations in Operative Command Table
	L	X	X	X	X	X	X	Power down ***(Note 17)***
Any State Other than Listed above	H	H	X	X	X	X		Refer to operations in Operative Command Table
	H	L	X	X	X	X	X	Begin clock suspend next cycle ***(Note 18)***
	L	H	X	X	X	X	X	Exit clock suspend next cycle
	L	L	X	X	X	X	X	Maintain clock suspend

H = High level, L = Low level, X = High or Low level (Don't care)

Notes 17: Self refresh can be entered only from the both banks idle state. Power down can be entered only from both banks idle or row active state.

Notes 18: Must be legal command as defined in Operative Command Table

Package Description



Controlling Dimension: Millimeters

SYM.	DIMENSION(MM)			DIMENSION(INCH)		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	—	1.20	—	—	0.047
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.90	1.00	1.10	0.035	0.039	0.043
b	0.30	—	0.45	0.012	—	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	20.82	20.95	21.08	0.820	0.825	0.830
E	10.03	10.16	10.29	0.395	0.400	0.405
H_E	11.56	11.76	11.96	0.455	0.463	0.471
e	—	0.80	—	—	0.031	—
L	0.40	0.50	0.60	0.016	0.020	0.024
L1	—	0.80	—	—	0.031	—
Y	—	—	0.10	—	—	0.004
ZD	—	0.88	—	—	0.031	—
θ	0°	—	10°	0°	—	10°

Revision History

Revision No.	History	Draft Date	Editor	Remark
0.1	Initial Release.	Aug. 2014	Ternence Chen	N/A
1.0	First SPEC. release.	Aug. 2014	Ternence Chen	N/A